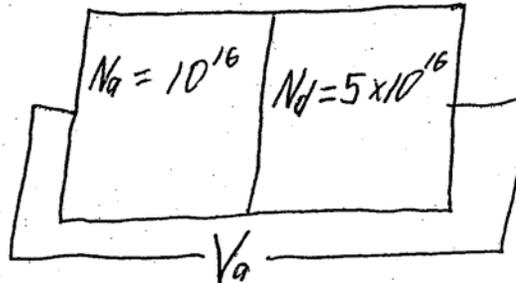


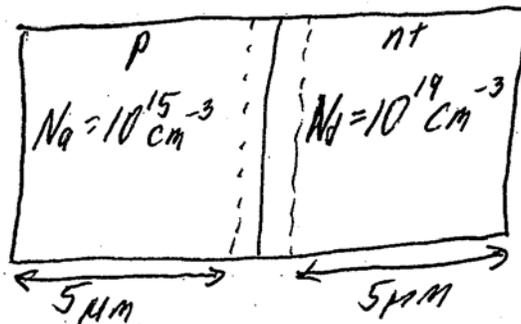
Homework # 4
 EE 3161 - Spring 2008
 Due Friday, March 28 in class

- 1) Problem 6.10 of Pierret.
- 2) Assume the *ideal* silicon diode below.
 - a) Make a quantitative sketch of the carrier concentrations across the diode for forward and reverse bias.
 - b) For a small forward bias of 0.2V, what is the total excess hole charge injected into the n-region if the area of the diode is 1 cm^2 ? Is this equal to the total excess electron charge in the p-region?
 - c) What is J_0 for the diode? If we increase the doping of the p-region to $N_a = 1 \times 10^{19} \text{ cm}^{-3}$, how does J_0 change (state which terms change and in which direction)?

Area = 1 cm^2
 $\tau_n = \tau_p = 1 \mu\text{s}$



- 3) A *real* silicon p-n junction has $N_a = 5 \times 10^{16} \text{ cm}^{-3}$ in the p-region and $N_d = 2 \times 10^{16} \text{ cm}^{-3}$ in the n-region. Assume the diode area is 1 cm^2 and $\tau_n = \tau_p = 1 \mu\text{s}$.
 - a) If we apply a reverse bias of 5V, what is the junction leakage current? What is the source of this current?
 - b) Can you derive a condition where the ideal diode equation leakage dominates?
 - c) What is the reverse bias breakdown voltage for this diode?
 - d) What is W at V_{br} ?
- 4) A $p-n^+$ diode (shown below) has an n^+ region doped at 10^{19} cm^{-3} and a p region doped at 10^{15} cm^{-3} . At what level of forward bias would an appreciable amount (0.1V) of voltage be dropped across the bulk regions? Assume $\tau_n = \tau_p = 1 \mu\text{s}$.



5) [Problem 2, midterm exam #2, spring 2007]

In the reverse-biased diode below, a narrow beam of light is scanned across a p-n junction. The recombination/generation time is $0.1\mu\text{s}$.

- Sketch the current produced by the light as a function of x across the entire device.
- The light has a cross-sectional area of $1\mu\text{m}^2$ (ignore diffraction). The diode is $10\mu\text{m}$ wide (along y) and $10\mu\text{m}$ thick (along z), and is doped at 10^{16} cm^{-3} on both sides. Estimate the current through the device if i) the light is off and ii) if the light is centered on the depletion region and generates $G_L=10^{23}\text{ cm}^{-3}\text{ s}^{-1}$.

